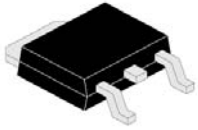


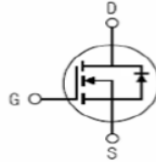
# N-Channel Power MOSFET

# CDD20N03



TO-252 (DPAK)

Inner Equivalent Principium Chart



TO-252 (DPAK)  
 SMD Plastic Package

## Features

1.  $R_{DS(ON)} < 35m\Omega @ V_{GS}=10V$
2. High density cell design for ultra low  $R_{dson}$
3. Fully characterized avalanche voltage and current
4. Excellent package for good heat dissipation

## Applications

1. Power switching application
2. Hard switched and high frequency circuits
3. Uninterruptible power supply

## Description

The CDD20N03 uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications. The package form is TO-252, which accords with the RoHS standard.

## Maximum Ratings ( $T_a=25^\circ C$ unless otherwise specified)

DESCRIPTION	SYMBOL	VALUE	UNIT
Drain-Source voltage	$V_{DSS}$	30	V
Gate-Source voltage	$V_{GS}$	$\pm 12$	V
Drain Current-Continuous	$I_D$	20	A
Pulsed Drain Current <sup>1</sup>	$I_{DM}$	80	A
Maximum Power Dissipation	$P_D$	32.5	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	150, -55 to +150	$^\circ C$

## Thermal Characteristic

DESCRIPTION	SYMBOL	VALUE	UNIT
Thermal Resistance, Junction-to-Case <sup>2</sup>	$R_{\theta JC}$	3.846	$^\circ C/W$

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise specified)**

DESCRIPTION	SYMBOL	Test Conditions	VALUE			Unit
			Min	Typ	Max	
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	V <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	30	-	-	V
Drain to Source Leakage Current (25°C)	I <sub>DSS</sub>	V <sub>DS</sub> = 30, V <sub>GS</sub> = 0V			1.0	μA
Gate to Source Forward Leakage	I <sub>GSS(F)</sub>	V <sub>GS</sub> = +12V,			0.1	μA
Gate to Source Reverse Leakage	I <sub>GSS(R)</sub>	V <sub>GS</sub> = -12V,			-0.1	μA
<b>On Characteristics 3)</b>						
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	0.7		2.5	V
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 10A			35	mΩ
Forward Trans conductance	g <sub>fs</sub>	V <sub>DS</sub> = 15V, I <sub>D</sub> = 2A		3		S
Pulse width t <sub>p</sub> ≤ 380μs, δ ≤ 2%						
<b>Dynamic Characteristics 4)</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V V <sub>DS</sub> = 50V, f=1.0 MHz		247		pF
Output Capacitance	C <sub>oss</sub>			34		
Reverse Transfer Capacitance	C <sub>rss</sub>			19.5		
<b>Rssistive Switching Characteristics 4)</b>						
Turn-On Delay Time	td(on)	V <sub>DD</sub> = 15V, I <sub>D</sub> = 3A V <sub>GS</sub> = 10V, R <sub>G</sub> = 1Ω,		6		ns
Rise Time	tr			15		
Turn-Off Delay Time	td(off)			15		
Fall Time	tf			10		
Total Gate Charge	Qg	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 3A, V <sub>DD</sub> = 15V		6		nC
Gate-Source Charge	Qgs			1		
Gate to Drain ("Miller") Charge	Qgd			1.3		
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <sup>3</sup>	V <sub>SD</sub>	I <sub>S</sub> = 20A, V <sub>GS</sub> = 0V			1.5	V
Continuous Source Current <sup>2</sup> (Body Diode)	I <sub>S</sub>				20	A

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

### Test Circuit and Electrical Characteristics

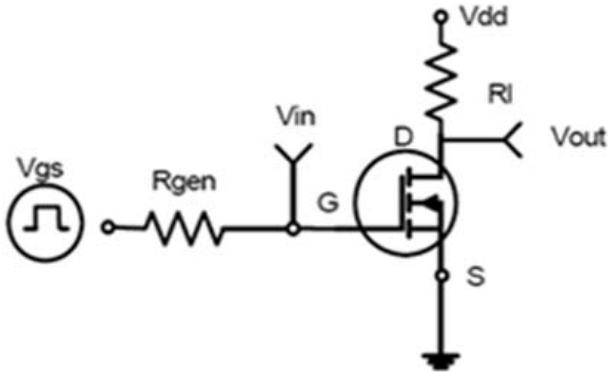


Figure 1: Switching Test Circuit

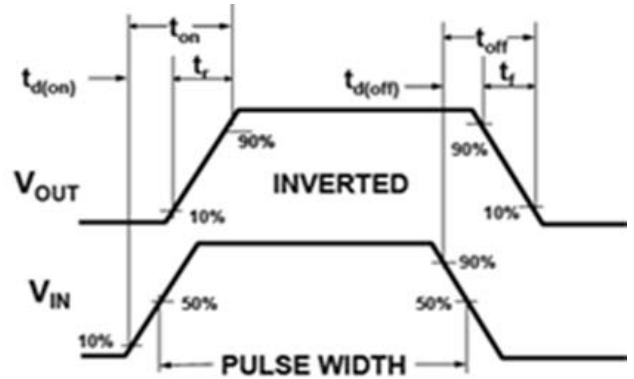


Figure 2: Switching Waveforms

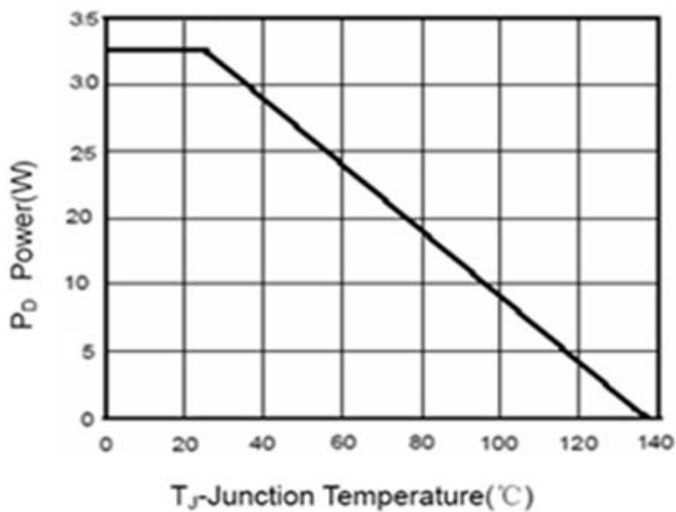


Figure 3 Power Dissipation

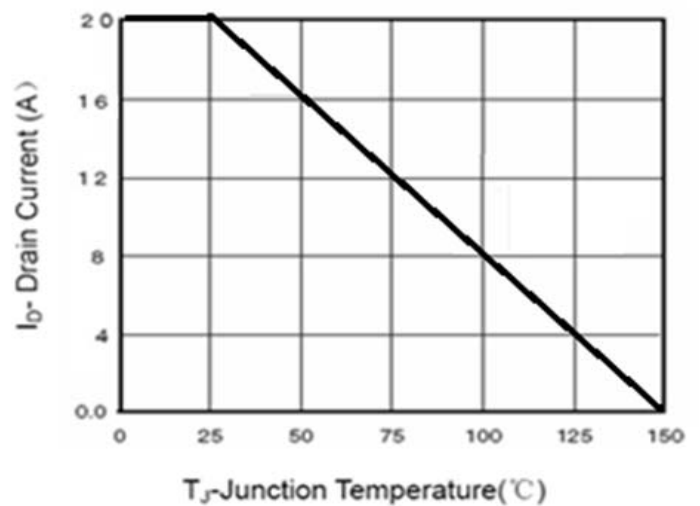


Figure 4 Drain Current

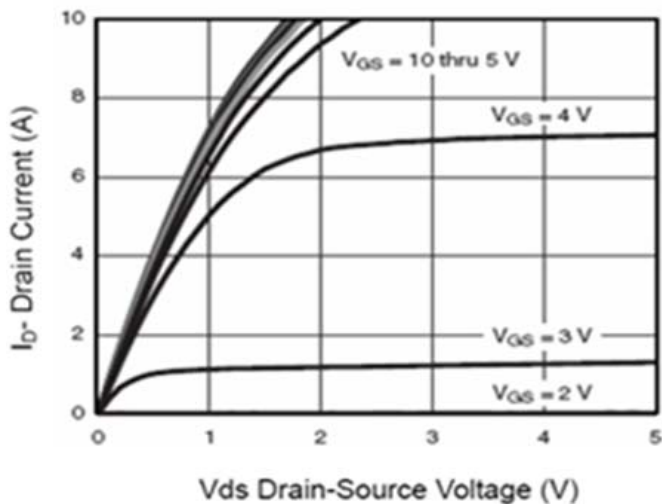


Figure 5 Output Characteristics

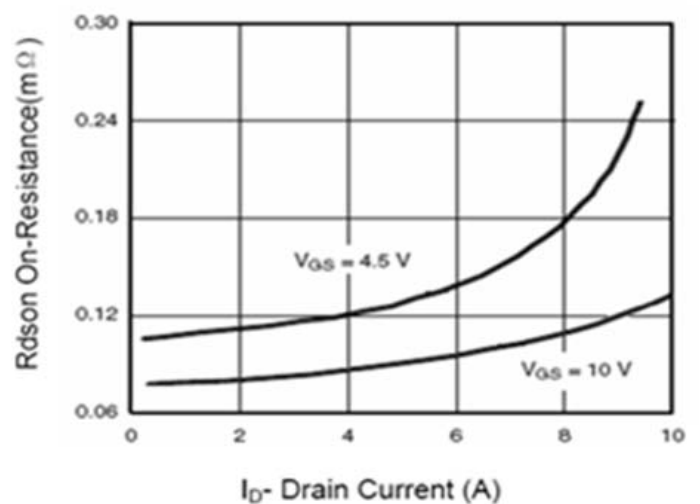
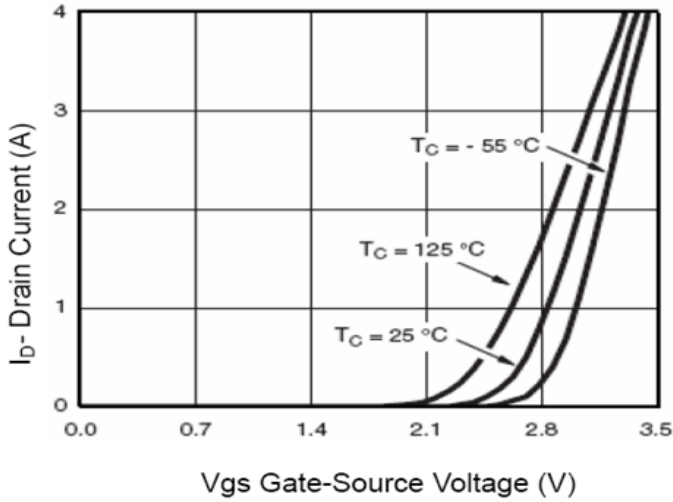
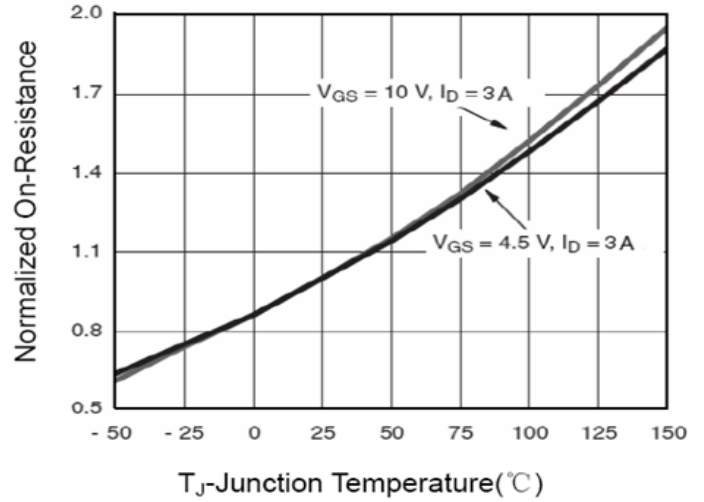


Figure 6 Drain-Source On-Resistance

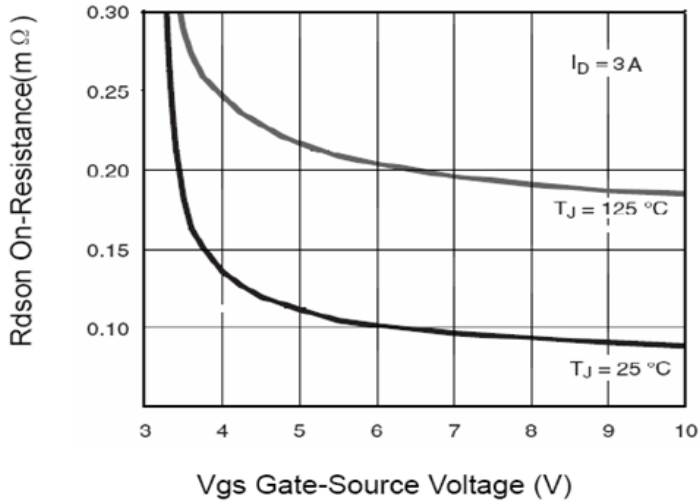
**Typical Electrical And Thermal Characteristics**



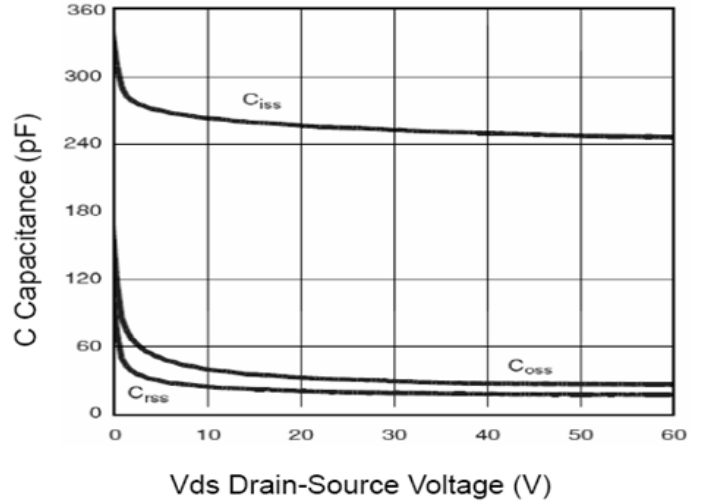
**Figure 7 Transfer Characteristics**



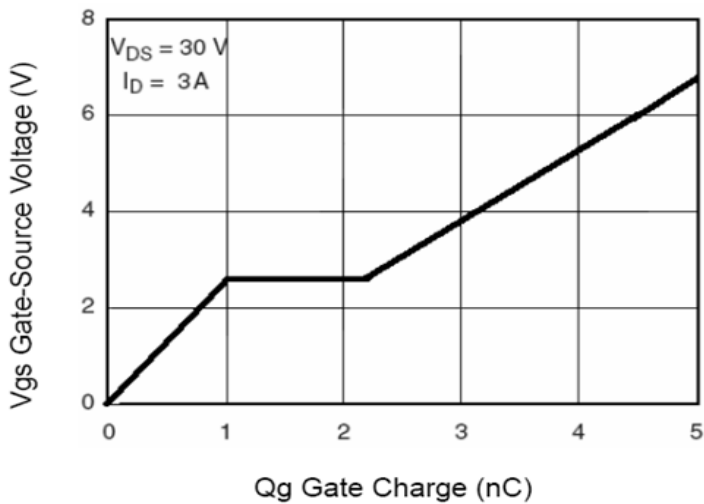
**Figure 8 Drain-Source On-Resistance**



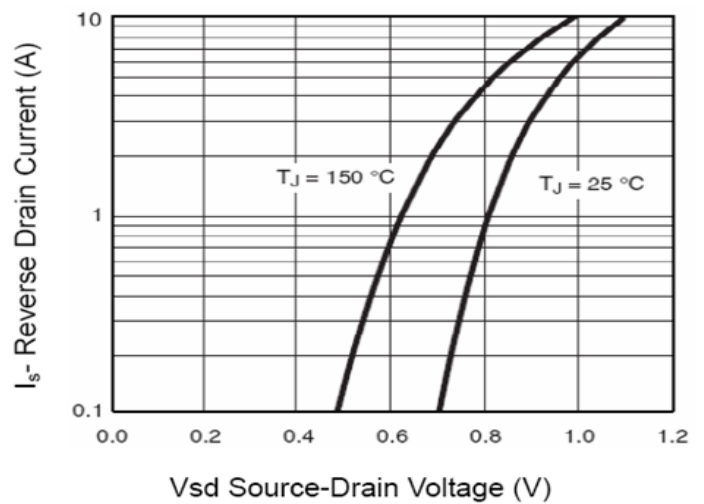
**Figure 9 Rdson vs Vgs**



**Figure 10 Capacitance vs Vds**

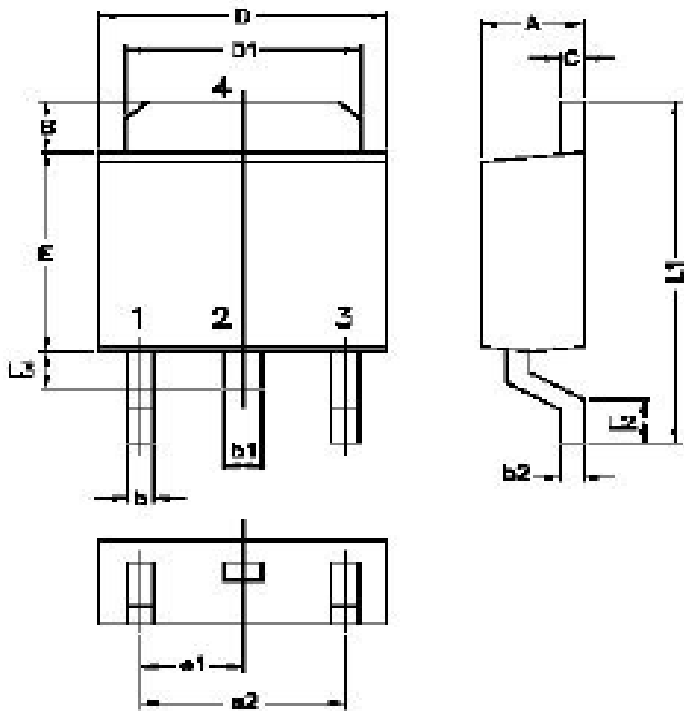


**Figure 11 Gate Charge**

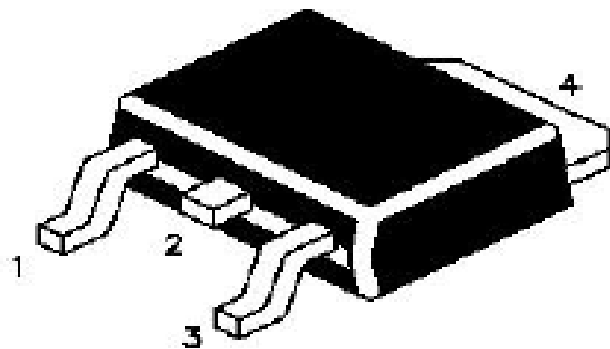


**Figure 12 Source- Drain Diode Forward**

### Package Details



DIM	MIN.	MAX.
A	2.20	2.40
B	1.30	1.50
b	0.55	0.65
b1	0.75	0.85
b2	0.46	0.58
C	0.46	0.58
D	6.40	6.60
D1	5.20	5.40
E	5.40	5.60
e1	2.25	2.35
e2	4.50	4.70
L1	9.25	9.75
L2	0.5	—
L3	0.90	1.10



#### PIN CONFIGURATION

1. T1 MAIN TERMINAL 1
2. T2 MAIN TERMINAL 2
3. G GATE
4. FIN (T2)



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## Customer Notes

## Component Disposal Instructions

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2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

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